

Description

1mm dia active area low dark current InGaAs Quadrant Photodiode with a P on N construction and 20 μ m wide gaps. It is packaged in aTO5 with a hermetic ultra flat fused silicon window cap.

Features

- 1 mm dia active area
- Small gap
- Low dark current
- Low crosstalk
- Planar structure MN+ InP substrate with 4 top anode contact

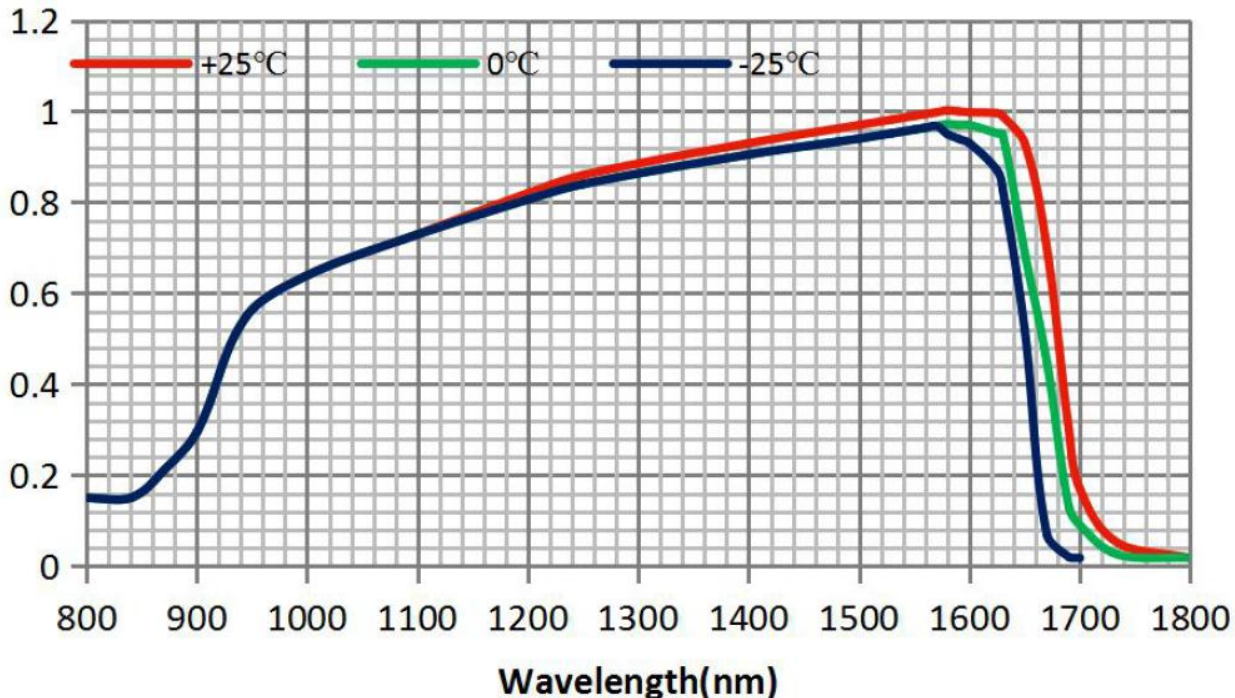
General Ratings

- High linearity
- High reliability

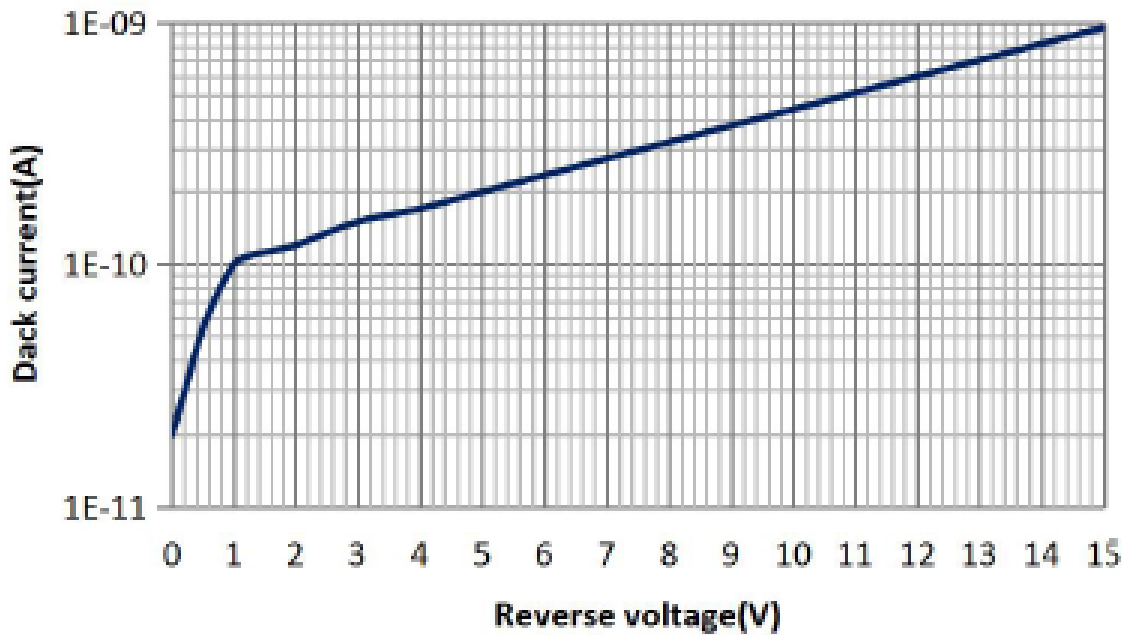
Applications

- Laser beam position sensors
- Optical tweezers
- Laser guidance
- Temperature measurement
- Process controlling

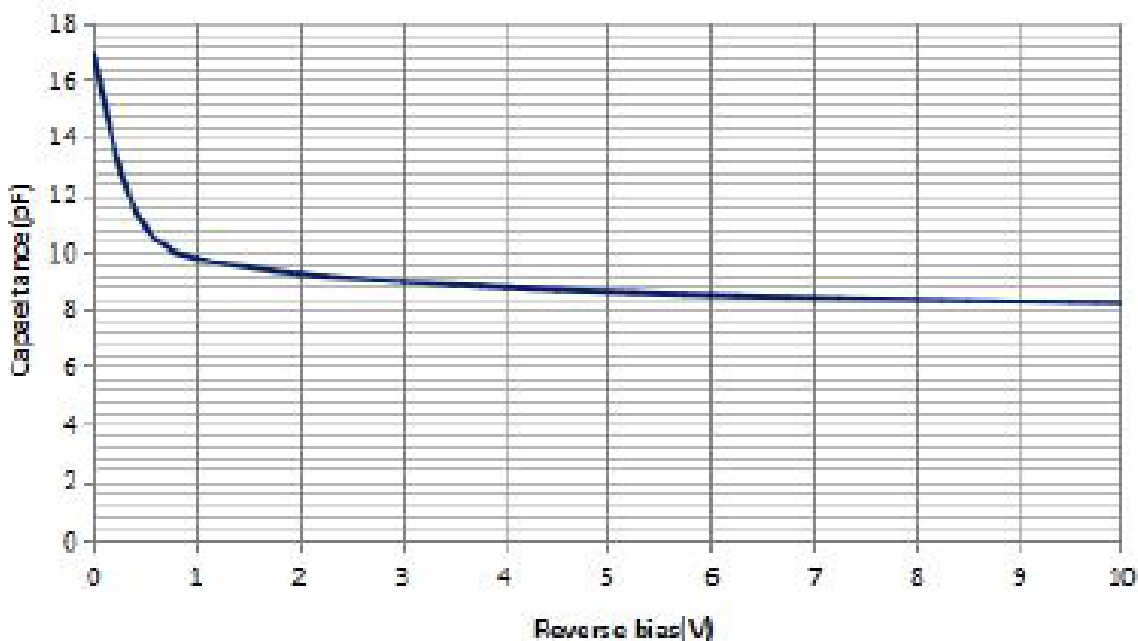
Spectral Response



Dark Current versus Reverse Bias Voltage



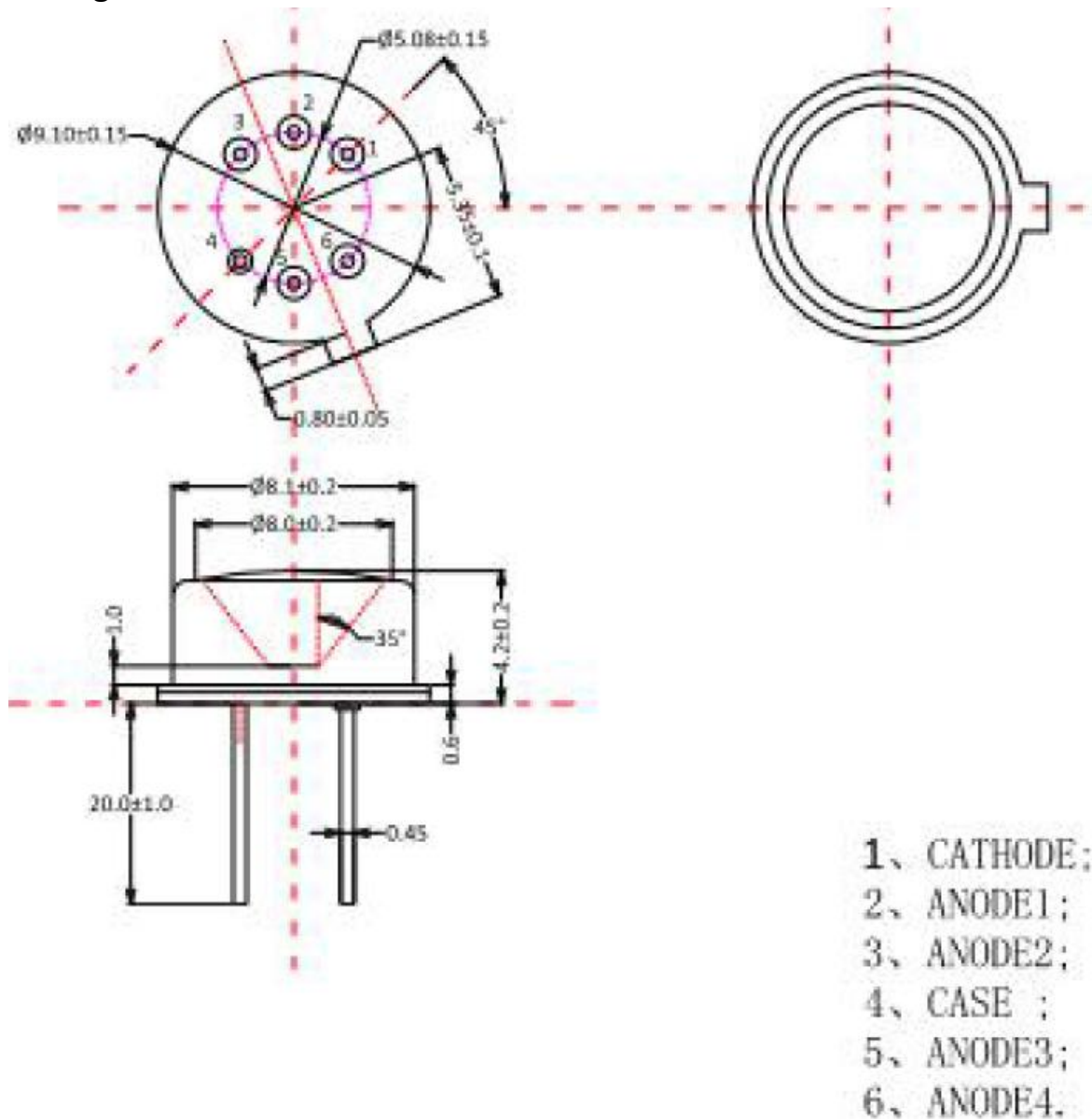
Relative Junction Capacitance versus Bias Voltage



E-O Parameters and Maximum Ratings (@+25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Chip size	Dia.			Φ 1		mm
Gap	d	element to element		20		μ m
Dark current	I_D			25	100	nA
Rise time	t_R	f=1MHz; λ =1550nm; VR=5V, RL=50 Ω		1	2	ns
Temp coefficient of I_D	TC _{IO}			0.18		times/°C
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=10\mu$ A Ev=0lx	40			V
Junction Capacitance	C_J	$V_R=0$ V f=1MHz		16.95		nF
		$V_R=5$ V f=1MHz		8.6		pF
Cross talk Channel- to -Channel		850-1700nm, Adjacent Channels, VR=5V			2	%
Uniformity of each Element	δ_{RE}	$V_R=5$ V, λ =1500nm, ϕ e=10 μ W			2	%
Saturation power	L	$V_R=5$ V,	10			mw
Photo sensitivity	S_R	1310nm		0.9		A/W
		1550nm		0.95		
Spectral Application Range	λ_{range}		800		1700	nm
Spectral Response-Peak	λ_p			1300		nm
Shunt resistance	R_{sh}	$V_R=10$ mV	75			M Ω
Rsh Temperature Coefficient	TC R _{sh}	VR=10mV		0.18		%/°C
Angular Resp 50% Resp Pt	$\theta_{1/2}$			\pm 55		Degrees

Package



All Dimensions in "mm".

The information in this data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omissions. The specifications are subject to change without notice.